



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
	36m $Ω$ @ V _{GS} = -4.5V		-6.2A
-20V	56mΩ @ V _{GS} = -2.5V	U-DFN2020-6 Type E	-5.0A
	75mΩ @ V _{GS} = -1.8V	7,50 =	-4.2A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

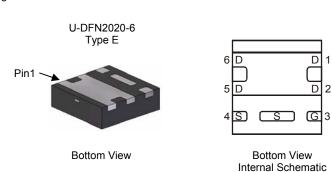
- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

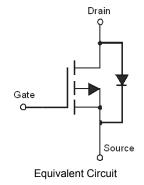
Features

- 0.6mm profile ideal for low profile applications
- PCB footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.0065 grams (approximate)





Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2066UFDE-7	U-DFN2020-6 Type E	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



PC = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September) Dot Denotes Pin 1

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	[3	С		D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Correct (Note EVV - 45V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-6.2 -4.9	Α
Continuous Drain Current (Note 5) V _{GS} = -4.5V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-7.5 -5.9	Α
Continuous Drain Current (Note EVV = 4.9)/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-4.2 -3.4	А
Continuous Drain Current (Note 5) V _{GS} = -1.8V	t<5s	T _A = +25°C T _A = +70°C	I _D	-5.2 -4.1	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-25	Α		
Maximum Continuous Body Diode Forward Current (Note 5)		ls	2.5	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)		P_{D}	0.66	W
The second Description to Australia (Alata 0)		-	189	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	t<5s R ₀ JA		°C/W
Total Power Dissipation (Note 5)		P_{D}	2.03	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	Б	61	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{ hetaJc}$	9.3	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

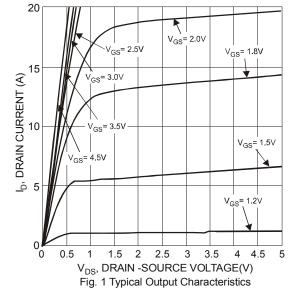
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				I.	I.		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12.0V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.4		-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	25	36		$V_{GS} = -4.5V$, $I_D = -4.6A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	33	56	mΩ	$V_{GS} = -2.5V, I_D = -3.8A$	
	, ,	_	50	75		$V_{GS} = -1.8V, I_D = -2.0A$	
Forward Transfer Admittance	Y _{fs}	_	9	_	S	$V_{DS} = -10V, I_{D} = -4.5A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_S = -2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		1537	_	pF	101/1/	
Output Capacitance	Coss		146	_	pF	V _{DS} = -10V, V _{GS} = 0V -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	127	_	pF	1 = 1.0WH12	
Gate Resistance	R_g		10.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Q_g	_	14.4	_		10)/)/ 15)/	
Gate-Source Charge	Q_{gs}	_	2.6	_	nC	$V_{DS} = -10V, V_{GS} = -4.5V$ $I_{D} = -4.5A$	
Gate-Drain Charge	Q_{gd}	_	2.7	_		ID = -4.5A	
Turn-On Delay Time	t _{D(on)}	_	13.7	_			
Turn-On Rise Time	t _r	_	14.0	_		$V_{DD} = -10V$, $V_{GS} = -4.5V$, $R_G = 6\Omega$,	
Turn-Off Delay Time	t _{D(off)}	_	79.1	_	ns	$R_L = 10\Omega, I_D = -1A$	
Turn-Off Fall Time	t _f		35.5	_			

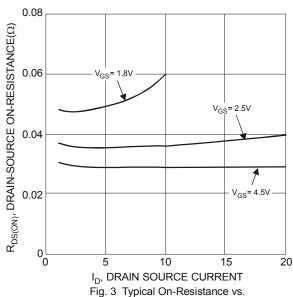
Notes:

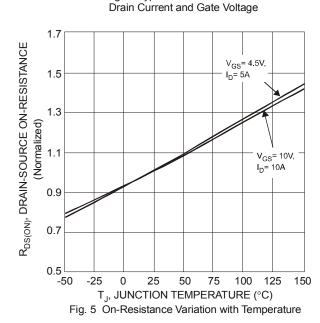
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



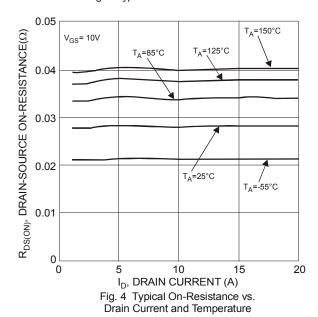


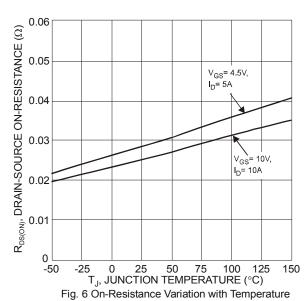






20 $V_{DS} = 5.0V$ 15 $V_{DS} = 5.0V$ $V_{DS} = 5.0V$ $V_{DS} = 5.0V$ $V_{A} = 85^{\circ}C$ $V_{A} = 125^{\circ}C$ $V_{A} = 125^{\circ}C$ $V_{A} = 150^{\circ}C$ $V_{A} = 150$





DMP2066UFDE



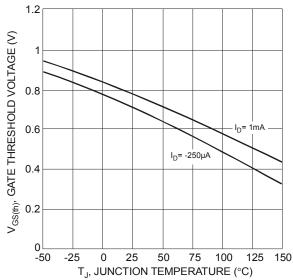


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

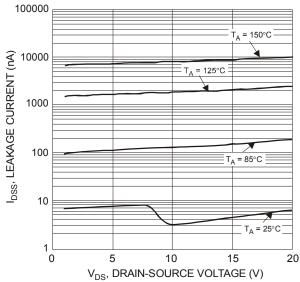
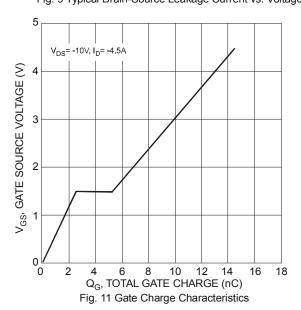
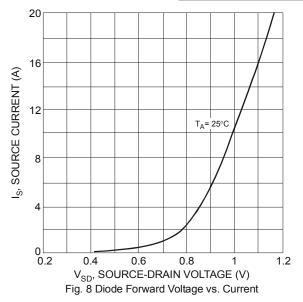
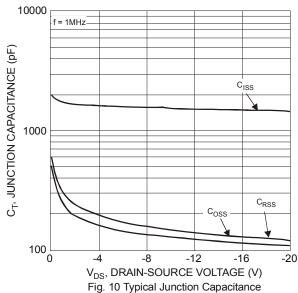
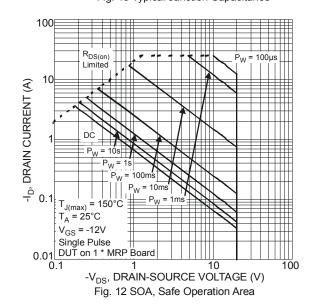


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

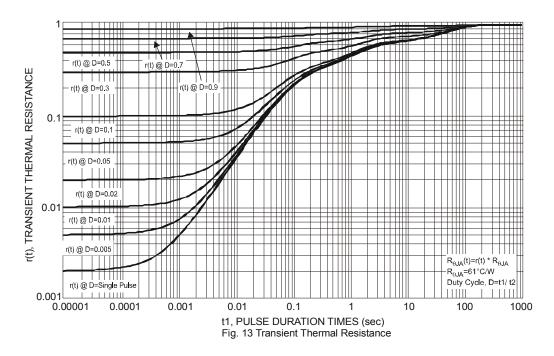




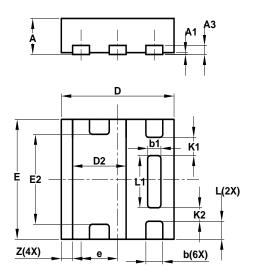








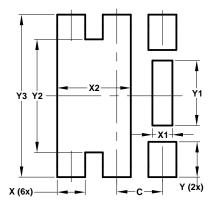
Package Outline Dimensions



U-DFN2020-6										
Type E										
Dim	Dim Min Max Typ									
Α	0.57	0.63	0.60							
A1	0	0.05	0.03							
А3	-	-	0.15							
b	0.25	0.35	0.30							
b1	0.185	0.285	0.235							
D	1.95	2.05	2.00							
D2	0.85	1.05	0.95							
Е	1.95	2.05	2.00							
E2	1.40	1.60	1.50							
е	_	_	0.65							
L	0.25	0.35	0.30							
L1	0.82	0.92	0.87							
K1	-	-	0.305							
K2	_	_	0.225							
Z	-	-	0.20							
All	Dimens	ions in	mm							



Suggested Pad Layout



Dimensions	Value				
Dilliensions	(in mm)				
С	0.650				
Х	0.400				
X1	0.285				
X2	1.050				
Υ	0.500				
Y1	0.920				
Y2	1.600				
Y3	2.300				

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